

Dual N-Channel 20-V (D-S) MOSFET

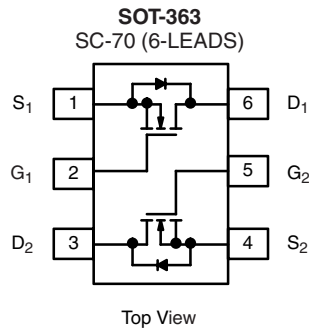
| PRODUCT SUMMARY | | |
|-----------------|---------------------------|-----------|
| V_{DS} (V) | $R_{DS(on)}$ (Ω) | I_D (A) |
| 20 | 0.385 at $V_{GS} = 4.5$ V | 0.70 |
| | 0.630 at $V_{GS} = 2.5$ V | 0.54 |

FEATURES

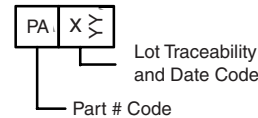
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFETs: 2.5 V Rated
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE
Available



Marking Code



Ordering Information: Si1902DL-T1-E3 (Lead (Pb)-free with Tape and Reel)
Si1902DL-T1-GE3 (Lead (Pb)-free and Halogen-free)

| ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted | | | | | |
|--|----------------|---------------|--------------|------|---|
| Parameter | Symbol | 5 s | Steady State | Unit | |
| Drain-Source Voltage | V_{DS} | 20 | | V | |
| Gate-Source Voltage | V_{GS} | ± 12 | | | |
| Continuous Drain Current ($T_J = 150$ °C) ^a | I_D | $T_A = 25$ °C | 0.70 | 0.66 | A |
| | | $T_A = 85$ °C | 0.50 | 0.48 | |
| Pulsed Drain Current | I_{DM} | 1.0 | | | |
| Continuous Source Current (Diode Conduction) ^a | I_S | 0.25 | 0.23 | | |
| Maximum Power Dissipation ^a | P_D | $T_A = 25$ °C | 0.30 | 0.27 | W |
| | | $T_A = 85$ °C | 0.16 | 0.14 | |
| Operating Junction and Storage Temperature Range | T_J, T_{stg} | - 55 to 150 | | °C | |

| THERMAL RESISTANCE RATINGS | | | | | |
|--|--------------|------------|---------|---------|------|
| Parameter | | Symbol | Typical | Maximum | Unit |
| Maximum Junction-to-Ambient ^a | $t \leq 5$ s | R_{thJA} | 360 | 415 | °C/W |
| | Steady State | | 400 | 460 | |
| Maximum Junction-to-Foot (Drain) | Steady State | R_{thJF} | 300 | 350 | |

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

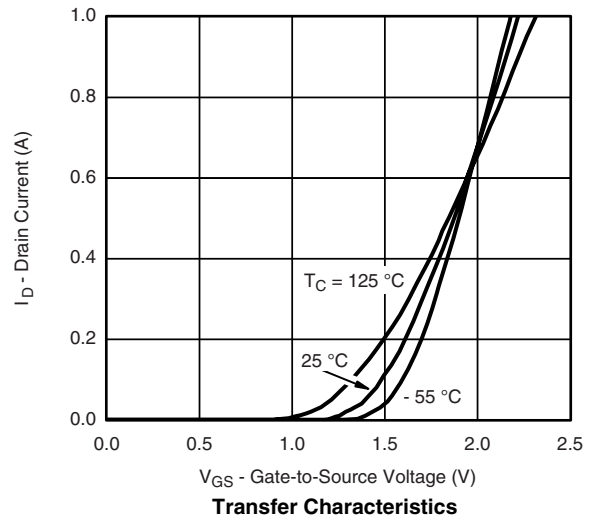
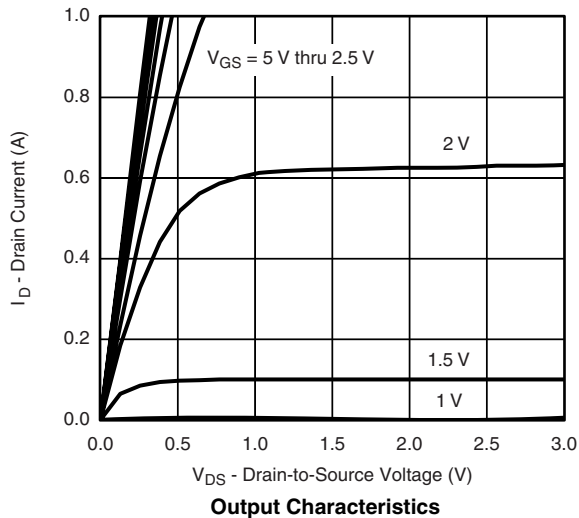
| SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted | | | | | | |
|--|--------------|---|------|-------|-----------|---------------|
| Parameter | Symbol | Test Conditions | Min. | Typ. | Max. | Unit |
| Static | | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$ | 0.6 | | 1.5 | V |
| Gate-Body Leakage | I_{GSS} | $V_{DS} = 0\text{ V}, V_{GS} = \pm 12\text{ V}$ | | | ± 100 | nA |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = 16\text{ V}, V_{GS} = 0\text{ V}$ | | | 1 | μA |
| | | $V_{DS} = 16\text{ V}, V_{GS} = 0\text{ V}, T_J = 85\text{ }^\circ\text{C}$ | | | 5 | |
| On-State Drain Current ^a | $I_{D(on)}$ | $V_{DS} \geq 5\text{ V}, V_{GS} = 4.5\text{ V}$ | 1.0 | | | A |
| Drain-Source On-State Resistance ^a | $R_{DS(on)}$ | $V_{GS} = 4.5\text{ V}, I_D = 0.66\text{ A}$ | | 0.320 | 0.385 | Ω |
| | | $V_{GS} = 2.5\text{ V}, I_D = 0.40\text{ A}$ | | 0.560 | 0.630 | |
| Forward Transconductance ^a | g_{fs} | $V_{DS} = 10\text{ V}, I_D = 0.66\text{ A}$ | | 1.5 | | S |
| Diode Forward Voltage ^a | V_{SD} | $I_S = 0.23\text{ A}, V_{GS} = 0\text{ V}$ | | 0.8 | 1.2 | V |
| Dynamic^b | | | | | | |
| Total Gate Charge | Q_g | $V_{DS} = 10\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 0.66\text{ A}$ | | 0.8 | 1.2 | nC |
| Gate-Source Charge | Q_{gs} | | | 0.06 | | |
| Gate-Drain Charge | Q_{gd} | | | 0.30 | | |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD} = 10\text{ V}, R_L = 20\text{ }\Omega$ $I_D \cong 0.5\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 6\text{ }\Omega$ | | 10 | 20 | ns |
| Rise Time | t_r | | | 16 | 30 | |
| Turn-Off Delay Time | $t_{d(off)}$ | | | 10 | 20 | |
| Fall Time | t_f | | | 10 | 20 | |
| Source-Drain Reverse Recovery Time | t_{rr} | $I_F = 0.23\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$ | | 20 | 40 | |

Notes:

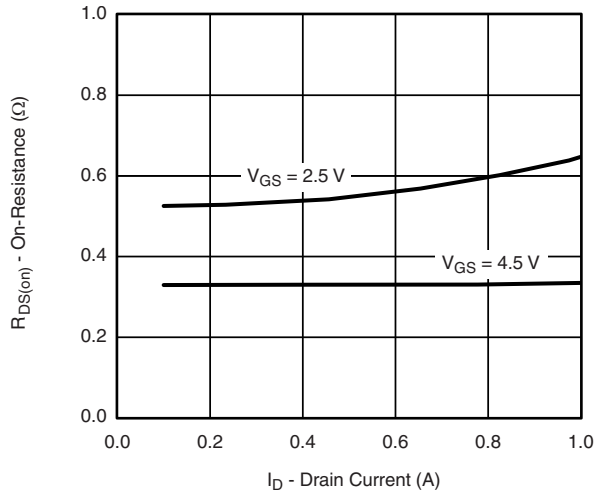
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

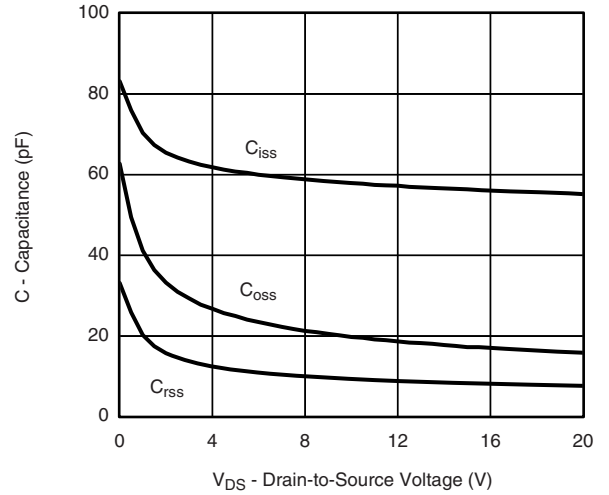
TYPICAL CHARACTERISTICS $25\text{ }^\circ\text{C}$, unless otherwise noted



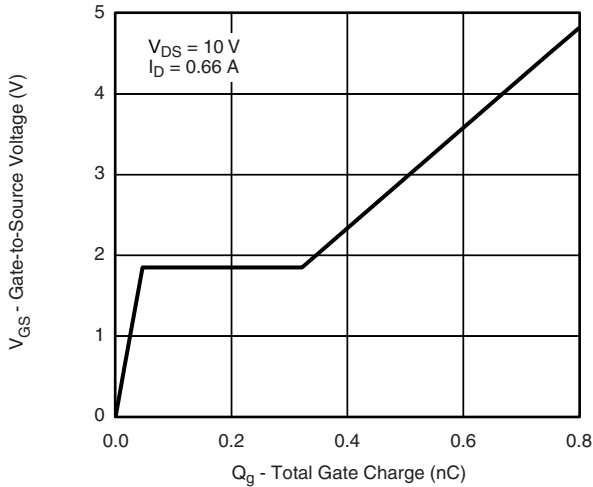
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



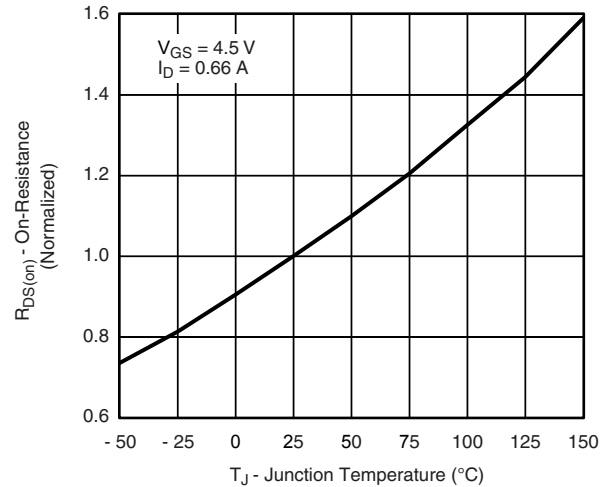
On-Resistance vs. Drain Current



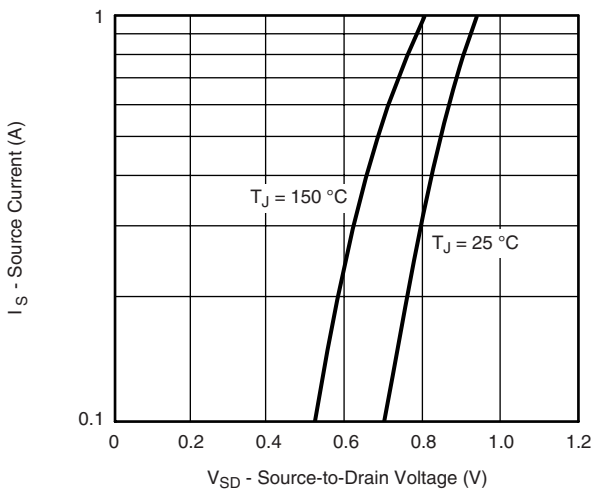
Capacitance



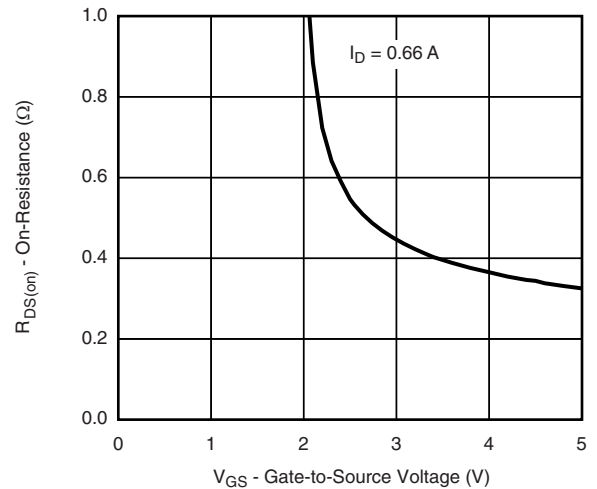
Gate Charge



On-Resistance vs. Junction Temperature

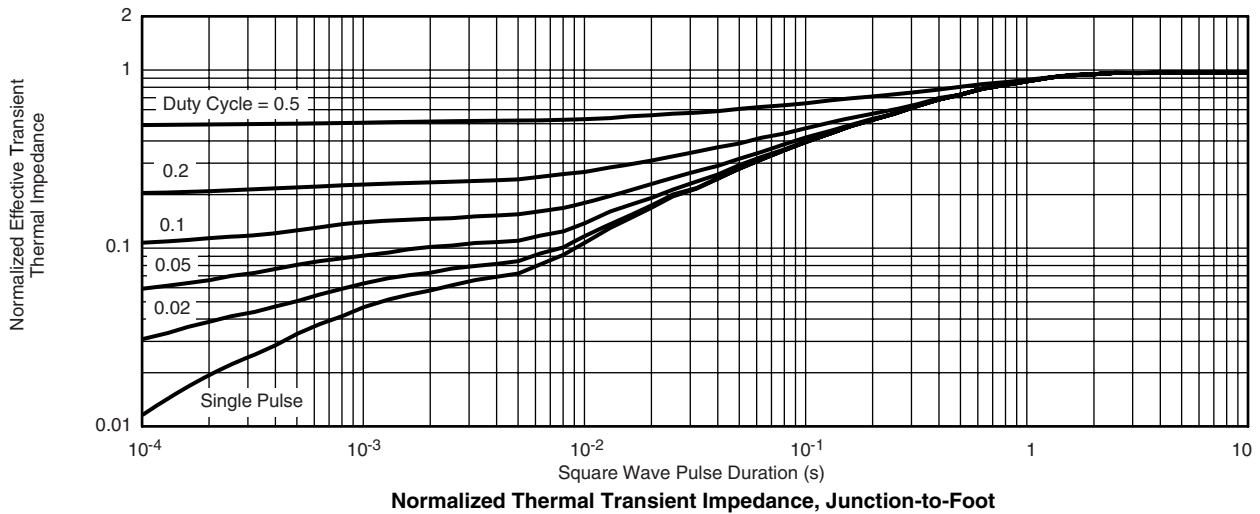
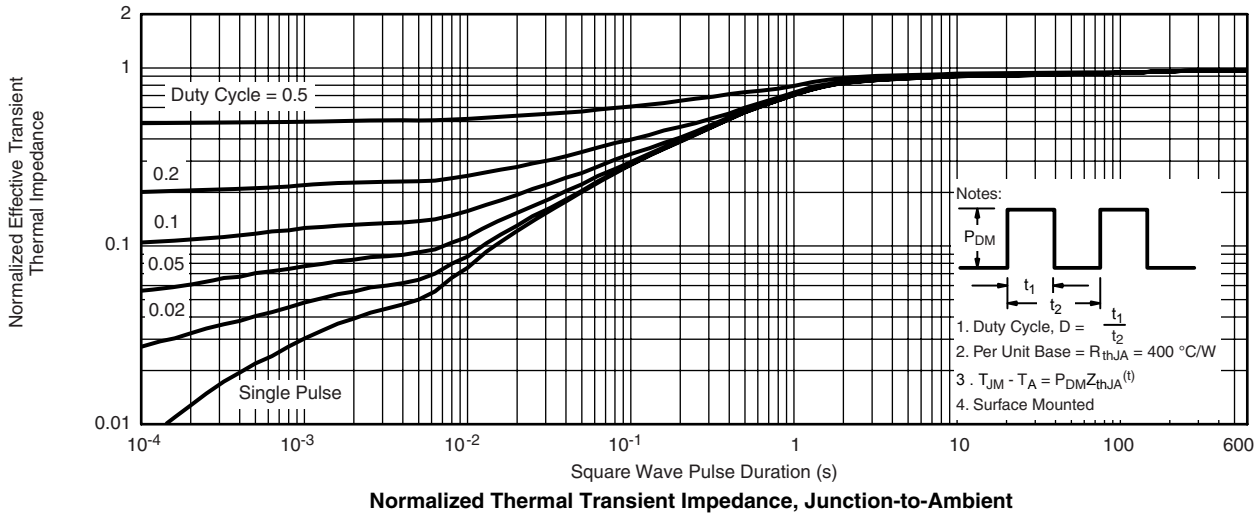
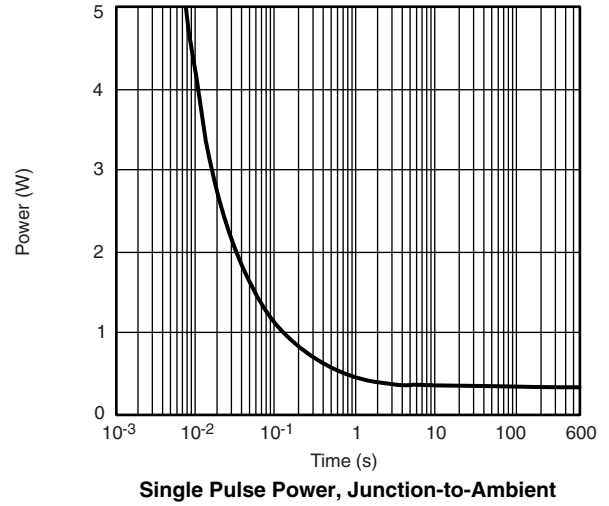
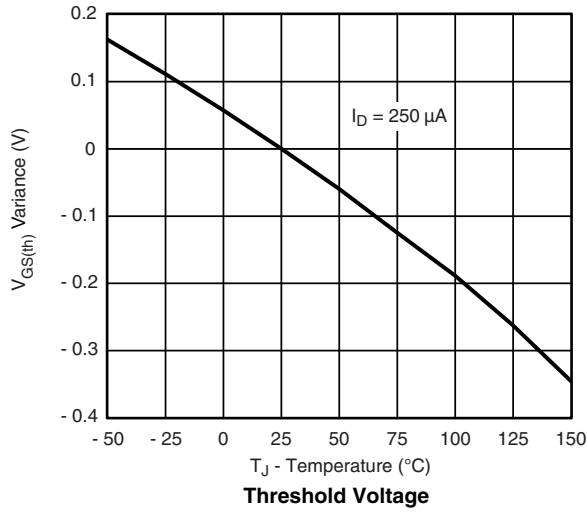


Surge-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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